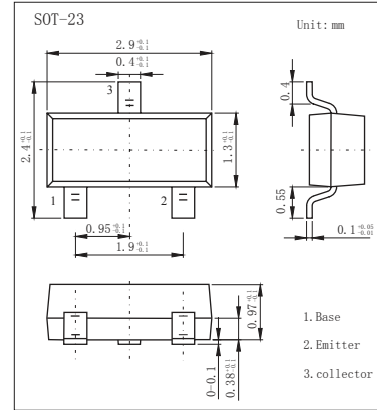


**NPN Transistors**  
**2SC2412**

■ Features

- Low Cob.Cob=2.0pF (Typ.)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	60	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	7	V
Collector current	I <sub>c</sub>	0.15	A
Collector power dissipation	P <sub>c</sub>	0.2	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = 50 μA, I <sub>E</sub> = 0	60			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>c</sub> = 1 mA, I <sub>B</sub> = 0	50			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 50 μA, I <sub>C</sub> = 0	7			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 7V, I <sub>C</sub> =0			100	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =50 mA, I <sub>B</sub> =5mA			0.4	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =50 mA, I <sub>B</sub> =5mA			1.2	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 6V, I <sub>c</sub> = 1mA	120		560	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 12V, I <sub>E</sub> = 0, f=1MHz		2	3.5	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 12V, I <sub>E</sub> = -2mA, f=100MHz	80			MHz

■ h<sub>FE</sub> Classification

Type	2SC2412/K-Q	2SC2412/K-R	2SC2412/K-S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS



炬芯微  
XUANXINWEI

SMD Type

Transistors

2SC2412

■ Typical Characteristics

